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- (54) **LOW IMPACT SIGNAL BUFFERING IN INTEGRATED CIRCUITS**
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- (58) **Field of Search** **326/41, 47, 101-103, 326/17; 257/202, 909**

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(57) **ABSTRACT**

A low impact buffer structure disposed in unused silicon area in a signal line routing channel between logic cell rows of an integrated circuit. In a buffer cell according to the invention, power to the buffer is provided by the power supply rails of one or more nearby logic cell rows. Both the connections to the supply rails and the connections between the transistors of the buffer cell are constructed of a polysilicon material and/or lower metal layer. In this manner, the buffer cell does not significantly impact the routing of metal signal lines in the signal line routing channel. In addition, the buffer cells can be arranged in a “staggered” configuration wherein separate buffers are provided in individual routing tracks of a signal line routing channel, further reducing the possibility of interference with normal signal routing. In addition, layout and routing tools according to the present invention are capable of monitoring the routing or loading of a signal line to determine when it reaches a length or load factor that may give rise to timing problems. When such a signal line is identified, the routing tool routes the signal line to the nearest available buffer cell or causes a buffer cell to be placed in a convenient location, preferably in the current routing channel. Following the routing process, updated netlist and timing information is generated for back-annotation to other design tools.

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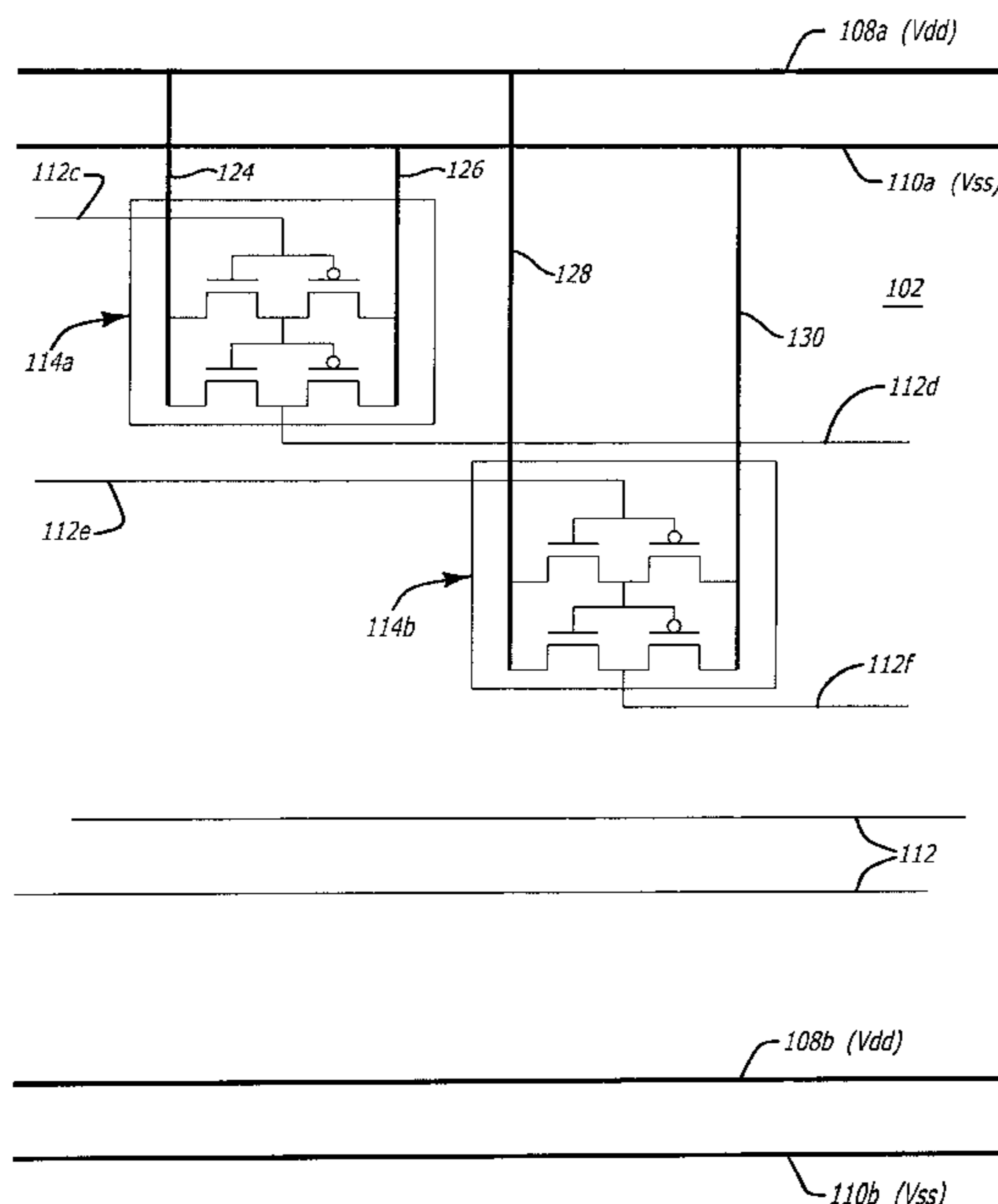
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14 Claims, 5 Drawing Sheets



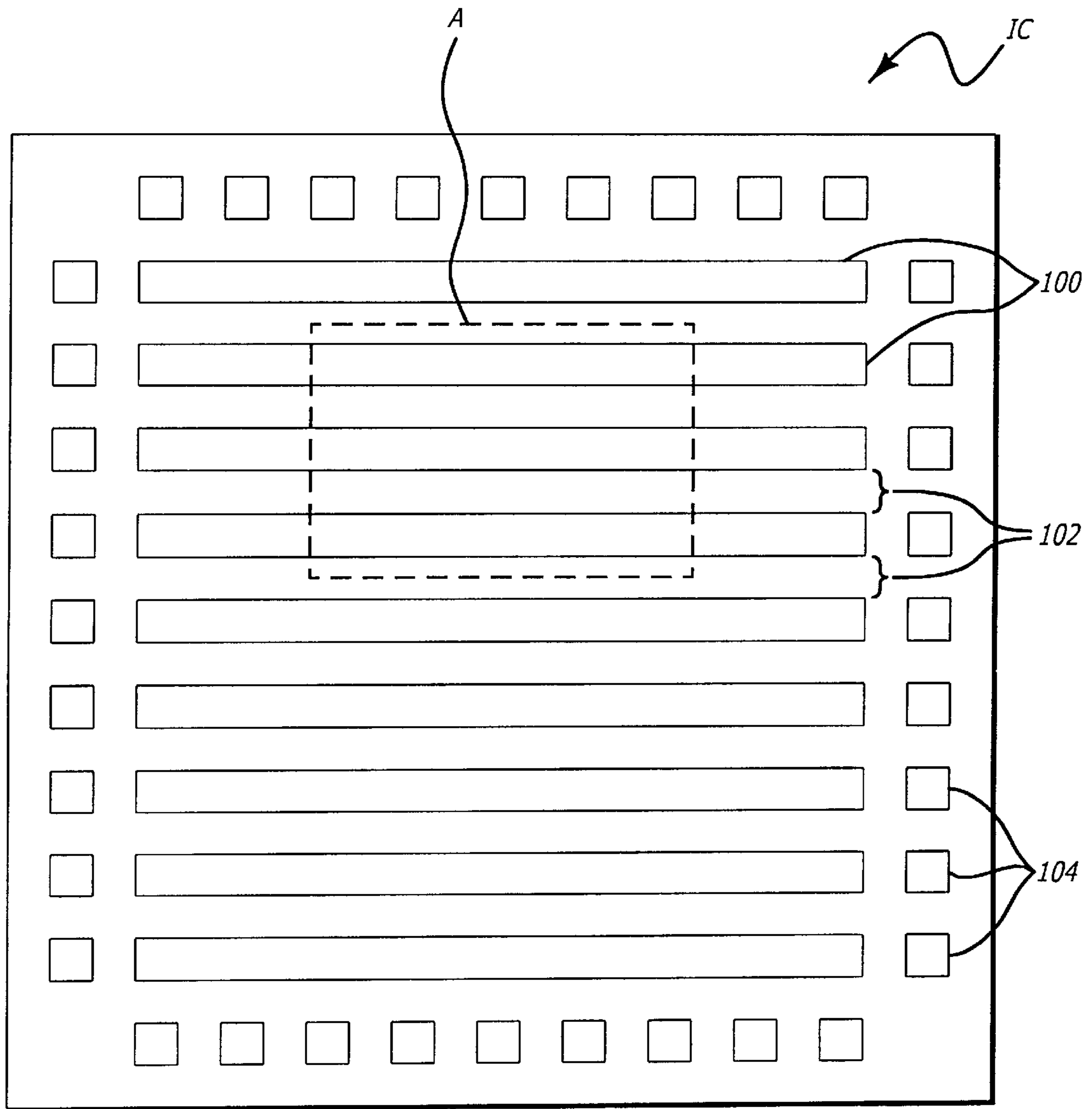


FIG. 1

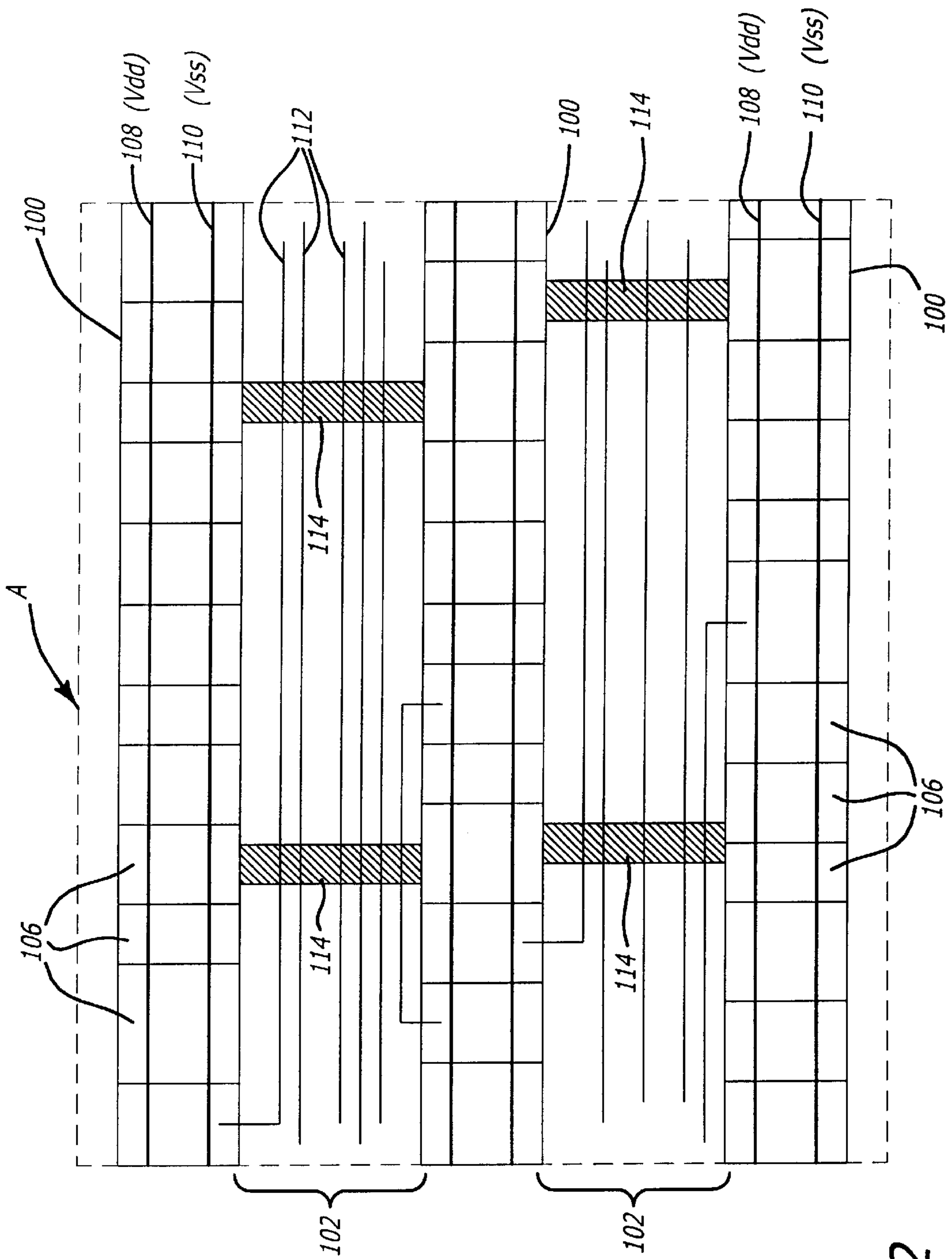


FIG. 2

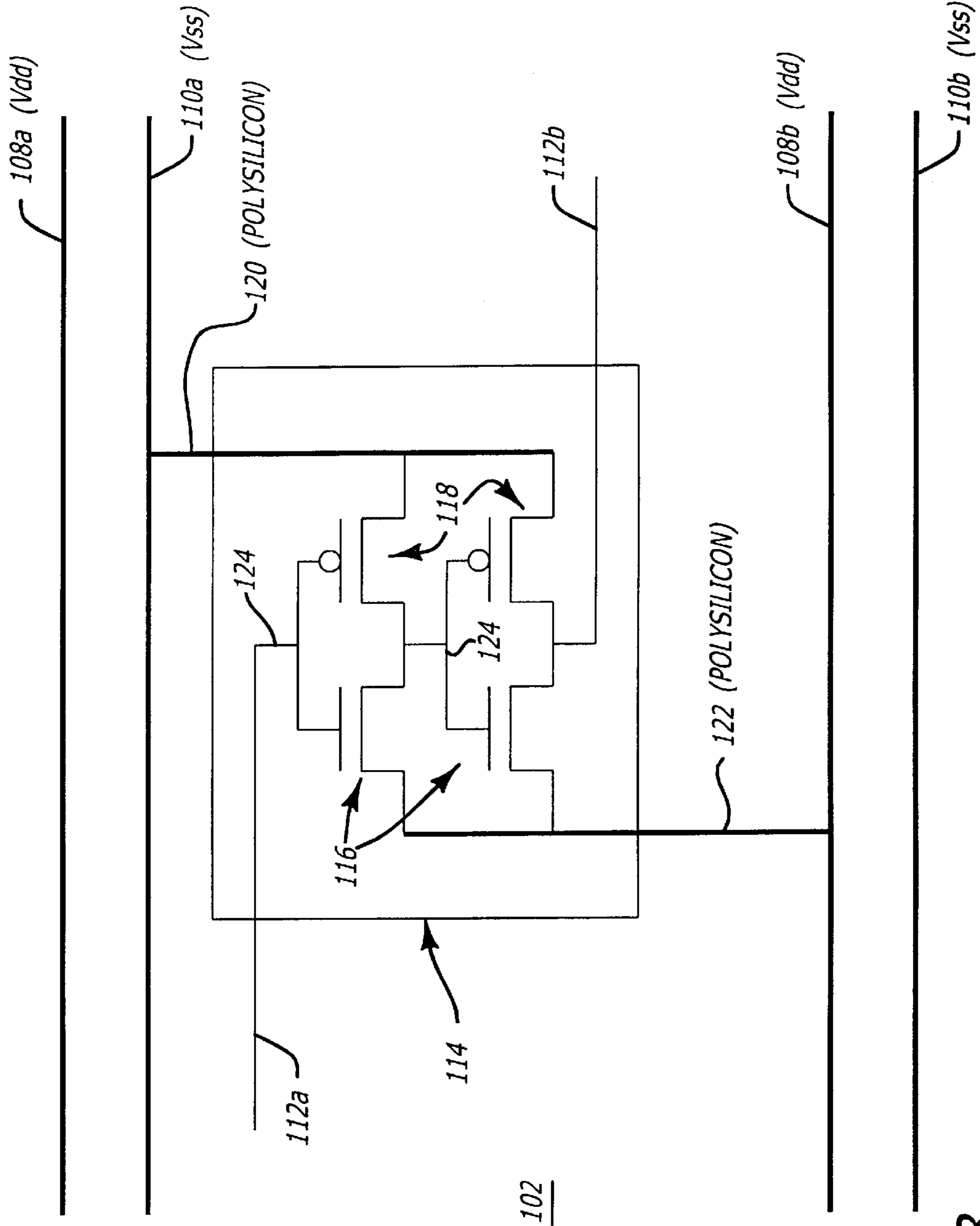


FIG. 3

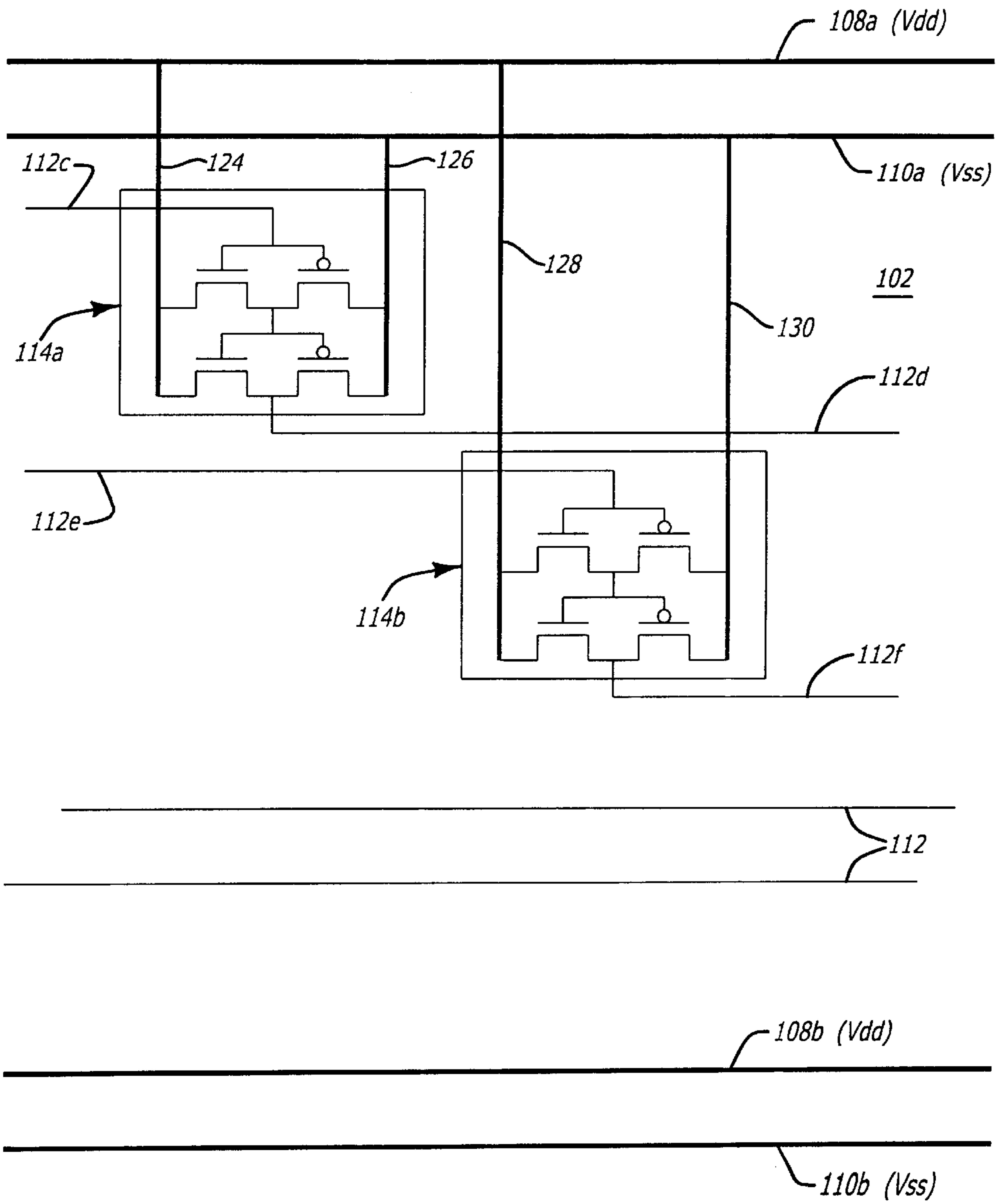


FIG. 4

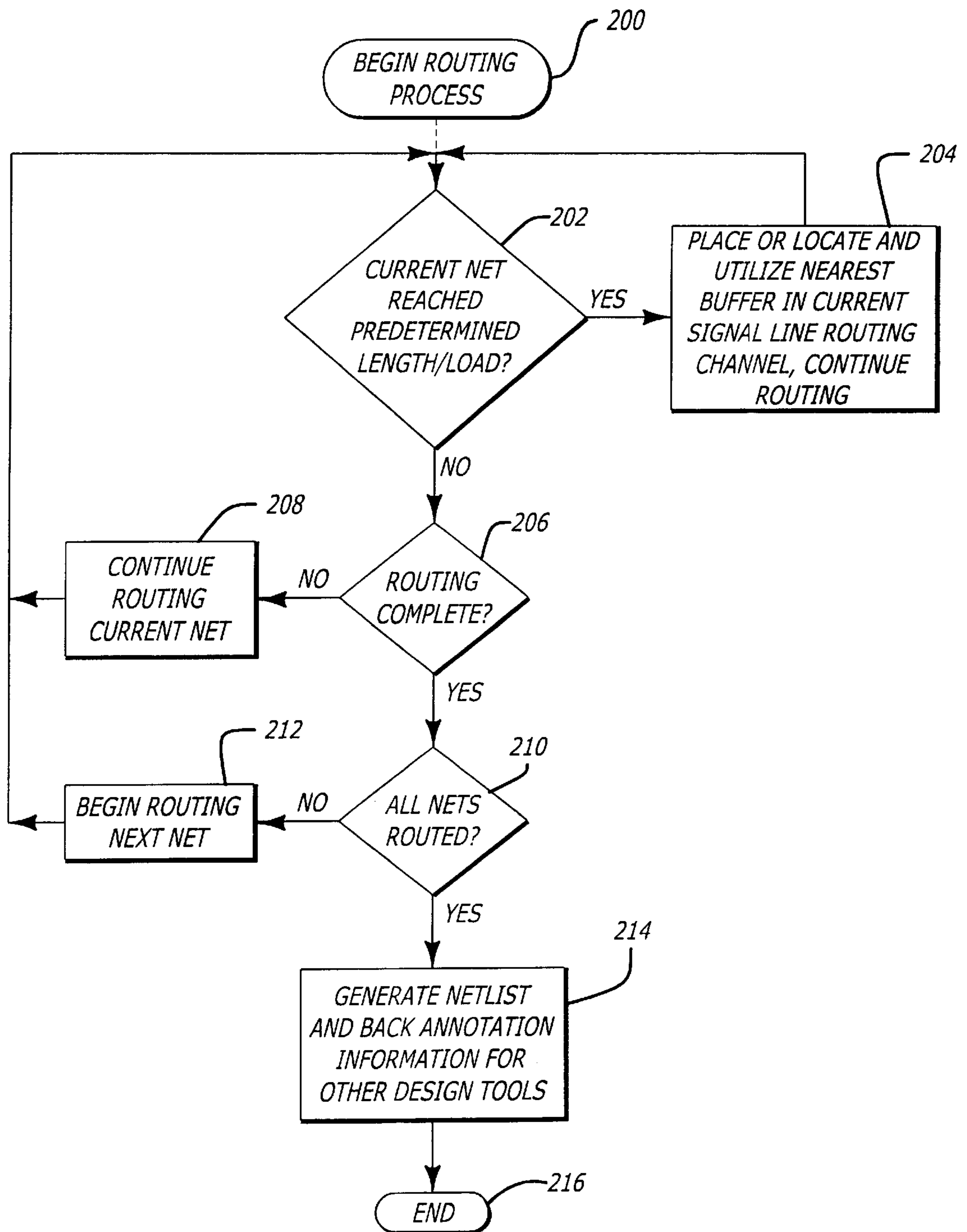


FIG. 5

LOW IMPACT SIGNAL BUFFERING IN INTEGRATED CIRCUITS

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to buffer circuitry fabricated on semiconductor dies, and more particularly to buffering circuitry located in the signal line routing regions or channels of integrated circuits.

2. Description of the Related Art

Integrated circuits have become key components of many consumer and commercial electronic products, often replacing discrete components and enhancing product functionality. The semiconductor processing technologies that produce these integrated circuits have advanced to the point where complete systems can now be reduced to a single integrated circuit or application specific integrated circuit (ASIC) device. These integrated circuits (also referred to as “chips”) may incorporate many functions that previously could not be implemented together on a single chip, including: microprocessors, digital signal processors, communication circuits, mixed signal and analog functions, large blocks of memory and high speed interfaces. The requisite level of integration, however, significantly complicates the design and manufacturing processes.

One difficult task facing integrated circuit manufacturers involves interconnecting the millions of logic gates and megabytes of memory that may be present on a chip. To aid in this task, new metallization schemes have been developed that allow five or more distinct “levels” or layers of metal interconnect wires, with pitches of $0.5\ \mu\text{m}$ and tighter on the first few layers. In most multiple layer metallization schemes, the various metal interconnect wires have different nominal widths and heights, different distances from transistor gates, and are insulated by oxide layers of varying thickness.

As semiconductor processes migrate further into the deep sub-micron range with multiple metal layers, increased circuit speeds allow the delay caused by the metal interconnect wires to reach the magnitude of active elements. The performance of sub-micron integrated circuitry can be dominated by propagation delays through the metal interconnect wires rather than the basic gate delays (i.e., transistor delays) of individual logic elements (also referred to as “logic cells” or “cells”). This phenomenon is attributable to a number of factors, including the fact that as the width of a wire shrinks in deep sub-micron designs, the resistance of the wire increases. Further, as transistor features shrink, their drive capability also decreases. It has been estimated that interconnect contributes as much as 70–80% of the total delay in integrated circuits implemented in $0.25\ \mu\text{m}$ process rules.

The aforementioned delays are manifested by “ramp time” effects. When a logic gate asserts or deserts a signal by applying or removing a voltage at one end of a signal line, the voltage at the input to a logic gate receiving the signal does not change instantaneously. Instead, there is a ramp time delay due principally to signal line impedance and capacitance. The voltage at the other end of the signal line “ramps” to the applied voltage, in a continuous, but not instantaneous, manner. Consequently, when a logic gate in one part of an integrated circuit sends a signal to a logic gate in another part of the integrated circuit, a small but noticeable propagation delay and “ramp” time is realized while the signal travels along a signal line. The propagation delay can be conceptualized as the delay between the time a signal transition is initiated and the time the signal begins ramping to an applied voltage.

An increase in average signal ramp times and propagation delays frequently results in a greater number of critical timing paths (e.g., signal paths in which best or worst case simulated propagation delays may approach the limits required for proper functionality). Many timing problems involve such critical timing paths, which effectively limit clock frequencies. Further, faster input signal ramp times may produce different results at a logic cell’s output than slower input signal ramp times. For these reasons, errors due to signal ramp times and/or propagation delays become a greater concern in sub-micron integrated circuit designs.

When performing timing analysis on an integrated circuit design, typical verification and synthesis tools estimate signal timing using floorplan or layout-based delay information supplied via back-annotation. For example, synthesis and floorplanning tools are commonly used to identify critical timing paths, while layout parasitic extraction (LPE) tools in conjunction with proprietary technology libraries are used to estimate the delay each critical path will experience in final layout. In the interest of improving manufacturing yields, functional simulations are often performed using these estimated delay values to verify operability. The terms “floorplan” and “layout” refer to the physical geometry of an integrated circuit or die. A floorplan consists of placed groupings of integrated circuit elements, including logic cells, that are used by signal wire routing tools in placing and functionally interconnecting the elements. A layout includes the completed integrated circuit design and is represented by a layout database containing information for generating the masks used to fabricate integrated circuits.

Within the core logic region of a typical integrated circuit, most of the digital logic cells are located in groupings of cells aligned in rows. These “cell rows” are separated by signal line routing channels in which the metal interconnect lines are disposed. Within each cell row, the individual logic cells are tightly grouped in order to conserve expensive silicon area and reduce the length of the signal lines. Layout tools place related logic gates as closely as practical, but signals must sometimes traverse relatively lengthy signal lines.

To correct resulting timing faults, a system designer can utilize buffering circuitry along failing critical paths to meet timing requirements. The “buffer” cells are logic cells which amplify a weak signal and can reduce ramp time on lengthy signal lines or heavily loaded signal lines. In large integrated circuits requiring many buffer cells, however, total die size is often negatively impacted due to the fact that the buffer cells themselves are included in and increase the size of the cell rows.

SUMMARY OF THE INVENTION

Briefly, the present invention provides a low impact buffer structure disposed in unused silicon area in a signal line routing channel between logic cell rows of an integrated circuit. The buffer structure allows a critical signal line to be buffered without negatively impacting the die size of the integrated circuit.

In one embodiment of a buffer cell according to the invention, power to the buffer is provided by the power supply rails of one or more nearby logic cell rows. Both the connections to the supply rails and the connections between the transistors of the buffer cell are constructed of a polysilicon material and/or lower metal layer. In this manner, the buffer cell does not significantly impact the routing of metal signal lines in the signal line routing channel. In addition, the buffer cells can be arranged in a “staggered” configuration

wherein separate buffers are provided in individual routing tracks of a signal line routing channel, further reducing the possibility of interference with normal signal routing. A reduction in die size is realized by the invention due to the fact that buffer circuitry is normally consumes space in the logic cell rows.

Further, layout and routing tools according to the present invention are capable of monitoring the routing or loading of a signal line to determine when it reaches a length or load factor that may give rise to timing problems. When such a signal line is identified, the routing tool routes the signal line to the nearest available buffer cell or causes a buffer cell to be placed in a convenient location, preferably in the current routing channel. Following the routing process, updated netlist and timing information is generated for back-annotation to other design tools.

BRIEF DESCRIPTION OF THE DRAWINGS

A better understanding of the present invention can be obtained with the following detailed description of the preferred embodiment is considered in conjunction with the following drawings, in which:

FIG. 1 is a top-level schematic diagram of an integrated circuit according to the present invention;

FIG. 2 is a schematic diagram showing portions of the integrated circuit of FIG. 1 in greater detail;

FIG. 3 is a schematic diagram providing details of a buffer circuit according to the present invention;

FIG. 4 is a schematic diagram of buffer circuits according to the present invention arranged in a staggered fashion; and

FIG. 5 is a flow chart of a signal routing methodology according to the present invention.

DETAILED DESCRIPTION OF INVENTION

Referring now to FIG. 1, a top-level schematic diagram of an exemplary integrated circuit IC according to the present invention is shown. The illustrated integrated circuit IC includes a plurality of cell rows **100** in which a large number of logic cells **106** (FIG. 2) are disposed. The cell rows **100** are separated in a typical fashion by signal line routing channels **102**. The signal line routing channels **102** are generally packed as densely as possible with metal signal lines which operably interconnect the logic cells **106**. Inputs and outputs to the integrated circuit IC are provided by bond pads **104**, which are electrically coupled to conductors in an integrated circuit package (not shown). As will be appreciated by those skilled in the art, the logic cell rows **100** can be arranged in a variety of ways. For example, the logic cell rows **100** can be placed as necessary to minimize die size when large blocks of circuitry, such as memory arrays and analog circuitry, are also present on the integrated circuit IC.

Exemplary details of a section A of the integrated circuit IC are shown in FIG. 2. The signal line routing channels **102** of the integrated circuit IC include several buffer banks or buffer cells **114** according to the present invention. The illustrated buffer banks or buffer cells **114** represent either pre-placed circuitry or areas in the signal line routing channels available for placement of buffer circuitry.

As will be appreciated by those skilled in the art, the precise nature of the logic cells **106** and the signal line **112** interconnects between the logic cells **106** is dictated by the functional design of the integrated circuit IC. Further, many different types of logic cells **106** are typically utilized in the design of an integrated circuit IC.

In the disclosed embodiment of the invention, the logic cells **106** of each of the logic rows **100** receive power from

a Vdd power supply rail **108**. A Vss or ground rail **110** is also provided to the logic cells **106** of each cell row **100**. In a multiple metal layer semiconductor process, the power supply rail **108** and the ground rail **110** are typically formed of a lower layer metal in order to minimize potential interference with signal line **112** routing.

As noted above, the cell rows **100** are separated by signal line routing channels **102**. Metallic signal lines **112** are illustrated as predominantly parallel lines located in the signal line routing channels **102**. It will be recognized by those skilled in the art that the metallic signal lines **112** can be formed of one or more metal layers in a semiconductor process employing multiple metal layers. The signal lines **112** provide interconnections between the logic cells **106** to allow for the communication of signals. The length of the various signal lines **112**, and the corresponding impedance-related effects of the signal lines **112**, lead to delays in signals communicated from one logic cell **106** to another logic cell **106**. These effects can be modeled to some extent by software design and verification tools, and can be compensated for by placing design rule limits on the lengths of a signal line **112**. Historically, however, signal lines often require buffering using buffer cells located in the cell rows **100**. While these buffers effectively reduced the effects of ramp time and capacitance-related problems, such a buffering approach tends to increase the size of the logic cell rows **100**, thereby increasing the overall size of the integrated circuit IC. According to the invention, signal lines **112** are buffered by employing buffer cells **114** disposed within the signal line routing channels **102**, rather than in the cell rows **100**.

Referring now to FIG. 3, details of an exemplary buffer cell **114** according to the present invention is shown. One end of a signal line **112a** is provided to the input of the buffer cell **114**. Signals provided to the buffer cell **114** via the signal line **112a** are buffered/amplified by the buffer cell **114** and provided to a second signal line **112b** at the output of the buffer cell **114**. Internally, the buffer cell **114** is comprised of a number of complimentary metal-oxide semiconductor (CMOS) transistors **116** and **118**. The transistors **116** and **118** can be interconnected in a variety of ways to provide the buffering function, with the relative sizes of the transistors **116** and **118** dictating the strengths of the buffer cell **114**, as well as the delay associated with the buffer cell **114**. Power to the internal transistors **116** and **118** of the buffer cell **114** is provided by electrically conductive connections **120** and **122**. More specifically, power to the buffer cell **114** is provided by a connection **122** coupling the buffer cell **114** to the Vdd power supply rail **108b** of a first logic cell row **100**. Likewise, the ground rail **110a** of a second cell row **100** is coupled to the transistors **114** and **116** of the buffer cell **114** by a second connection **120**.

Because the buffer cell **114** is implemented in a signal line routing channel **102**, it is desirable to keep both the buffer cell **114** and the power and ground connections **122** and **120** as "flat" as possible, meaning that the structures create as few metal signal line **112** blockages. In order to reduce the impact to the routing of the signal lines **112** (which typically utilize all of the metal layers), it may therefore be necessary and desirable to route the power and ground connections **122** and **120** using a polysilicon material. The polysilicon layer is typically formed at an earlier stage in semiconductor processes than the metal layers. Further, it is desirable that the internal interconnections between the transistors **116** and **118** of the buffer cell **114** are similarly routed in a polysilicon material or a first or lower metal layer in a multiple metal layer semiconductor process. By utilizing such materials,

metal signal lines **112** formed of upper metal layers can be routed over the buffer cell **114**. Such signal lines **112** have been omitted in the figures for sake of clarity.

Referring now to FIG. 4, a schematic diagram of buffer cells **114** arranged in a staggered fashion according to the present invention is shown. Two separate buffer cells **114a** and **114b** are illustrated in this alternate embodiment of the invention. Referring first to buffer cell **114a**, power is provided by a connection **124** to the Vdd power supply rail **108a** of a logic cell row **100**. The ground rail **110a** of the same logic cell row **100** is also coupled to the transistors of the buffer cell **114a**. The input of the buffer cell **114a** is coupled to a signal line **112c** and drives a signal line **112d**.

Power and ground connections to the transistors of the second buffer cell **114b** are provided by connections **128** and **130**, respectively, to the power supply rail **108a** and ground rail **110a** of the cell row **100**. The input of the buffer cell **114b** is coupled to a signal line **112e** and drives a signal line **112e**.

In the preferred embodiment of the invention, each buffer cell **114** is provided with separate power and ground connections, particularly if the connections are formed of a relatively high resistance polysilicon material. Polysilicon material typically has an ohms per square value which is approximately 100 times higher than that of the metal layer materials. In an embodiment wherein the power and ground connections are formed of polysilicon, providing separate connections for each buffer cell **114** reduces the possibility of resistive voltage drops which may diminish the drive capability of the buffer cell **114**. This results in a staggered configuration for the buffer cells **114a** and **114b** as shown in FIG. 4. In addition, the power and ground connections **124–130** are preferably kept as short as possible.

Further, it may be desirable to only use signal lines **112** with relatively small loading with the embodiments of the buffer cell **114** shown in FIG. 4. Heavily loaded signal lines **112** may require an amount of current out of the buffer cell **114** that causes significant resistive drops across the power and ground connections **124–130**.

The staggered arrangement of the buffer cells **114a** and **114b** also reduces the possibility of interference between signal lines **112**. Signal line routing channels **102** are sometimes divided into separate routing “tracks” by the routing tools. Each routing track or a portion of each routing track can be utilized for routing separate signal lines **112** on a specific metal layer. Preferably, the buffer cells **114a** and **114b**, as well as any additional buffer cells **114** (not shown) provided in a signal line routing channel **102**, are arranged such that the signal line **112** coupled to the output of one buffer cell **114** does not encroach upon the routing track(s) aligned with the inputs or outputs of other buffer cells **114** in the same signal line routing channel **102**.

Referring now to FIG. 5, a flow chart of signal routing methodology according to the present invention is shown. The routing methodology is capable of placing or utilizing buffer cells **114** located in the signal routing channels **102**. The signal routing methodology could be implemented in a design flow such as LSI Logic’s Flexstream Design Solution, or in any other proprietary or standardized routing methodology.

The disclosed embodiment of the invention commences in step **200** where the routing process begins. Signal line **112** routing typically follows placement of the logic cells **106** in the cell rows **100** in accordance with a layout “netlist.” In most integrated circuit design methodologies, a layout netlist and physical design exchange format (PDEF) file are

generated for use in the physical design or layout of the integrated circuit IC. The netlist reflects the interconnectivity of the logic elements of an integrated circuit IC, while the PDEF file contains information regarding the physical hierarchy of the logic elements. During the “place and route” procedure, a layout database is generated containing interconnected representations of the individual elements of an integrated circuit IC. A layout database is essentially a complete integrated circuit design and contains information for generating the masks used to fabricate an integrated circuit.

Following various other steps including the routing of a signal line **112**, the routing process proceeds to step **202** and the routing tool monitors the signal line **112** (also referred to as a “net” when combined with other signal lines **112**) it is currently routing to determine when a predetermined metal layer dependent threshold, such as length or load factor, is reached. When this occurs, the routing tool (in step **204**) places or locates the nearest buffer cell **114**, preferably in the current signal line routing channel **102**. The routing tool then continues routing from the output of the utilized buffer cell **114**, and continues to monitor the signal line **112** in step **202**.

If the signal line **112** has not reached the predetermined length/load factor as determined in step **202**, the routing process continues with step **206** to ascertain if the routing of the current signal line **112** is complete. If not, the routing process continues in step **208**. If routing of the current signal line **112** is complete as determined in step **206**, the routing process proceeds to step **210** to determine if all signal lines **112** or nets have been routed. If not, the routing tool begins routing the next signal line **112** in step **212**. Following either of steps **208** or **212**, the routing process returns to step **202** for continued monitoring of the routing of the current signal line **112**.

If all nets or signal lines **112** have been routed as determined in step **210**, the routing process continues in step **214** where netlist and back-annotation information for other design tools is generated. The routing process is then ended in step **216**.

The information generated in step **214** can be utilized by static timing analyzers and delay calculators. Static timing analyzers rely on timing models of all logic cell **106** circuit elements to compare total path delays between the synchronous elements with required signal setup and hold times, thus allowing all delay paths to be checked. Delay calculators may also be used in the static timing analysis process. When delay calculators are used, pre- and post-layout signal delay information is computed and back-annotated into HDL simulators and synthesis tools, and support static timing analysis tools as the basis for these tools internal delay analysis processes. Delay calculators preferably utilize a number of factors, such as pin-to-pin timing data, multiple input ramp times and support for conditional delays. Signal line modeling used in the design and verification processes estimate the effect of wire length and fan out on resistance, capacitance, and area.

Preferably, delay calculators capable of interfacing with all of the CAE tools are utilized in the design flow of the integrated circuit IC. Numerous delay calculators, such as LSIDELAY by LSI Logic Corporation are available for calculating such delays, and can produce files in a format suitable for back-annotation into the synthesis tools. Use of these software verification tools in conjunction with buffer cells **114** according to the invention may decrease development costs incurred by multiple design iterations.

Standardized file formats such as the standard delay format (SDF), the design exchange format (DEF), and the

physical design exchange format (PDEF) may be used to pass data between floor planning and the synthesis environment for interconnect delay modeling, although the invention is not limited in scope to use with any particular file formats.

CAE tools according to the present invention are able to account for delays introduced by the buffer cells 114. Any such switching delays, while generally undesirable, may be outweighed by improvements in signal integrity achieved by the reduction of signal ramp time effects accomplished by the buffer cells 114.

Thus, a buffer structure disposed in the unused silicon area in a signal line routing channel between logic cells rows of an integrated circuit has been described. The buffer structure is designed to minimize impact on signal line routing due to metal blockages. Power and ground connections to the internal components of the buffer structure, as well as connections between the transistors of the buffer structure are formed of a polysilicon and/or lower metal layer in order to achieve this result. Layout and routing tools have also been described which are capable of recognizing and utilizing such buffer structures.

The foregoing disclosure and description of the invention are illustrative and explanatory thereof, and various changes in the details of the illustrated apparatus and construction and method of operation may be made without departing from the spirit of the invention.

What is claimed is:

1. An integrated circuit manufactured in a semiconductor process utilizing multiple metal layers to form signal lines for communicating signals between logic gates, comprising:

plural rows of logic gates;

signal line routing channels separating the rows of logic gates; and

buffer circuits disposed in the signal line routing channels for buffering signals communicated between the logic gates,

wherein each of said buffer circuits has a separate electrical connection, not shared with any other buffer, to each of a power supply rail and a ground rail.

2. The integrated circuit of claim 1, wherein the first row of logic gates include a power supply rail and a ground rail, the buffer circuit being comprised of:

a plurality of transistors interconnected to amplify an input signal; and electrically conductive connections coupling the plurality of transistors to the power supply rail and the ground rail of the first row of logic gates.

3. The integrated circuit of claim 2, wherein the electrically conductive connections of the buffer circuit are formed of either a polysilicon material or a lower metal layer.

4. The integrated circuit of claim 2, wherein the electrically conductive connections of the buffer circuit are formed of a combination of polysilicon material and a lower metal layer.

5. The integrated circuit of claim 2, wherein the plurality of transistors are interconnected by a polysilicon material.

6. The integrated circuit of claim 2, wherein the plurality of transistors are interconnected by a combination of polysilicon material and a lower metal layer.

7. The integrated circuit of claim 1, wherein the transistors of the buffer circuit are complementary metal-oxide-semiconductor transistors.

8. The integrated circuit of claim 1, wherein the first and second rows of logic gates each include a power supply rail and a ground rail, the buffer circuit being comprised of:

a plurality of transistors interconnected to amplify an input signal;

a first electrically conductive connection coupling the plurality of transistors to the power supply rail of the first row of logic gates; and

a second electrically conductive connection coupling the plurality of transistors to the ground rail of the second row of logic gates.

9. The integrated circuit of claim 8, wherein the first and second electrically conductive connections of the buffer circuit are formed of either a polysilicon material or a lower metal layer.

10. The integrated circuit of claim 8, wherein the first and second electrically conductive connections of the buffer circuit are formed on a combination of a polysilicon material and a lower metal layer.

11. An integrated circuit manufactured in a semiconductor process utilizing multiple metal layers to form signal lines for communicating signals between logic gates, comprising:

a plurality of rows of logic gates;

a plurality of signal line routing channels separating the plurality of rows of logic gates;

a plurality of signal lines disposed in the signal line routing channels for communicating signals between the logic gates; and

a plurality of buffer circuits disposed in the plurality of signal line routing channels for amplifying signals on signal lines;

wherein each row of the plurality of rows of logic gates includes a power supply rail and a ground rail, and

wherein separate electrically conductive connections, not shared with any other buffer, are provided from each of the power supply rail and the ground rail included in an adjacent row of logic gates to each of the plurality of buffer circuits.

12. The integrated circuit of claim 11, wherein each of the plurality of buffer circuits is comprised of:

a plurality of transistors interconnected to amplify an input signal; and

electrically conductive connections coupling the plurality of transistors to the power supply rails and the ground rails of the plurality of rows of logic gates.

13. The integrated circuit of claim 12, wherein the electrically conductive connections of the buffer circuits are formed of either a polysilicon material or a lower metal layer.

14. The integrated circuit of claim 12 wherein each of the signal line routing channels is divided into a plurality of routing tracks for placement of signal lines, and wherein adjacent ones of the buffer circuits are disposed in a staggered configuration for receiving signal lines of different routing tracks.